Product data sheet

# 1. Product profile

## 1.1 General description

High-voltage, high-speed planar-passivated NPN power switching transistor in a SOT428 (D-PAK) surface mounted package.

#### 1.2 Features and benefits

- Low thermal resistance
- Fast switching

## 1.3 Applications

- Electronic lighting ballasts
- Inverters

- DC-to-DC converters
- Motor control systems

#### 1.4 Quick reference data

- V<sub>CESM</sub> ≤ 700 V
- Arr P<sub>tot</sub>  $\leq$  80 W

- $I_C \le 4 A$
- h<sub>FEsat</sub> = 12.5 (typ)

# 2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	base	mb	
2	collector	[1]	2
3	emitter		1—
mb	mounting base; connected to collector	1 3 SOT428 (D-PAK)	3 sym056

[1] It is not possible to make a connection to pin 2 of the SOT428 (D-PAK) package.



# 3. Ordering information

Table 2. Ordering information

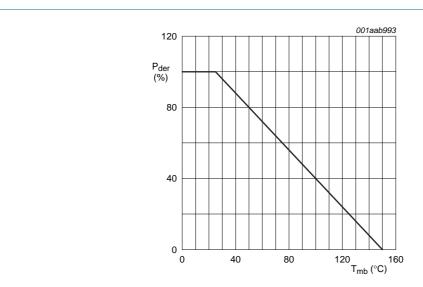
Type number	Package					
	Name	Description	Version			
BUJ103AD	D-PAK	plastic single-ended surface mounted package; 3 leads (one lead cropped)	SOT428			

# 4. Limiting values

#### Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CESM}$	peak collector-emitter voltage	$V_{BE} = 0 V$	-	700	V
$V_{CBO}$	collector-base voltage	open emitter	-	700	V
$V_{CEO}$	collector-emitter voltage	open base	-	400	V
I <sub>C</sub>	collector current (DC)		-	4	Α
I <sub>CM</sub>	peak collector current		-	8	Α
I <sub>B</sub>	base current (DC)		-	2	Α
$I_{BM}$	peak base current		-	4	Α
P <sub>tot</sub>	total power dissipation	$T_{mb} \le 25$ °C; see Figure 1	-	80	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-	150	°C



$$P_{der}(\%) = \frac{P_{tot}}{P_{tot(25 \, ^{\circ}C)}} \times 100\%$$

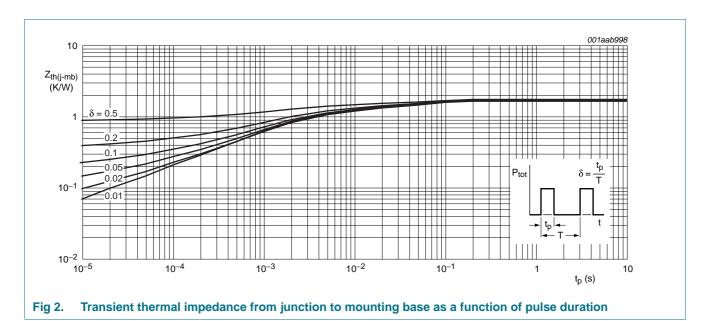
Fig 1. Normalized total power dissipation as a function of mounting base temperature

# 5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 2	-	-	1.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		<u>[1]</u> _	75	-	K/W

[1] Device mounted on a printed-circuit board; minimum footprint.



## 6. Characteristics

Table 5. Characteristics

 $T_{mb} = 25$  °C; unless otherwise specified.

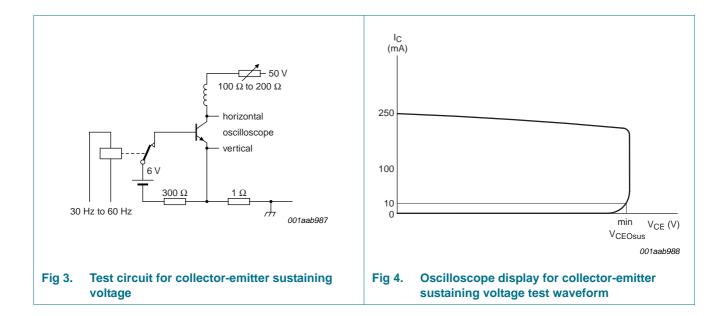
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
I <sub>CES</sub>	collector-emitter cut-off	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = V <sub>CESMmax</sub>	<u>[1]</u> -	-	1.0	mΑ
	current	$V_{BE} = 0 \text{ V}; V_{CE} = V_{CESMmax}; T_j = 125 ^{\circ}\text{C}$	<u>[1]</u> _	-	2.0	mΑ
I <sub>CBO</sub>	collector-base cut-off current	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = V <sub>CESMmax</sub>	<u>[1]</u> _	-	1.0	mΑ
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CEO} = V_{CEOMmax} = 400 \text{ V}$	[1] _	-	0.1	mA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 7 \text{ V}; I_{C} = 0 \text{ A}$	-	-	0.1	mΑ
V <sub>CEOsus</sub>	collector-emitter sustaining voltage	$I_B = 0$ A; $I_C = 10$ mA; $L = 25$ mH; see Figure 3 and 4	400	-	-	V
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 3.0 \text{ A}$ ; $I_B = 0.6 \text{ A}$ ; see <u>Figure 10</u>	-	0.25	1.0	V
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = 3.0 \text{ A}$ ; $I_B = 0.6 \text{ A}$ ; see <u>Figure 11</u>	-	0.97	1.5	V
h <sub>FE</sub>	DC current gain	$I_C = 1 \text{ mA}$ ; $V_{CE} = 5 \text{ V}$ ; see Figure 9	10	17	32	
		$I_C = 500 \text{ mA}; V_{CE} = 5 \text{ V}$	13	22	32	
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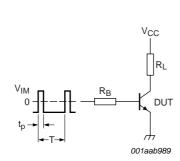
 Table 5.
 Characteristics ...continued

 $T_{mb} = 25$  °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
h <sub>FEsat</sub>	DC saturation current gain	$I_C = 2.0 \text{ A}; V_{CE} = 5 \text{ V}$	11	16	22	
		$I_C = 3.0 \text{ A}; V_{CE} = 5 \text{ V}$	-	12.5	-	
Dynamic o	characteristics					
Switching t	imes (resistive load); see Figure	<u>5</u> and <u>6</u>				
t <sub>on</sub>	turn-on time	$I_{Con} = 2.5 \text{ A}; I_{Bon} = -I_{Boff} = 0.5 \text{ A};$ $R_L = 75 \Omega$	-	0.52	0.6	μS
t <sub>stg</sub>	storage time		-	2.7	3.3	μS
t <sub>f</sub>	fall time		-	0.3	0.35	μS
Switching t	imes (inductive load); see Figure	<u>e 7</u> and <u>8</u>				
t <sub>stg</sub>	storage time	$I_{Con} = 2 \text{ A}; I_{Bon} = 0.4 \text{ A}; L_{B} = 1 \mu\text{H};$	-	1.2	1.4	μS
t <sub>f</sub>	fall time	$V_{BB} = -5 \text{ V}$	-	30	60	ns
Switching t	imes (inductive load); see Figure	<u>e 7</u> and <u>8</u>				
t <sub>stg</sub>	storage time	$I_{Con} = 2 \text{ A}; I_{Bon} = 0.4 \text{ A}; L_{B} = 1 \mu\text{H};$	-	-	1.8	μS
t <sub>f</sub>	fall time	$V_{BB} = -5 \text{ V; } T_j = 100 ^{\circ}\text{C}$	-	-	120	ns

[1] Measured with half sine-wave voltage (curve tracer).





 $V_{IM}$  = -6 V to +8 V;  $V_{CC}$  = 250 V;  $t_p$  = 20  $\mu s;$   $\delta$  =  $t_p/T$  = 0.01.

 $R_{\text{B}}$  and  $R_{\text{L}}$  calculated from  $I_{\text{Con}}$  and  $I_{\text{Bon}}$  requirements.

#### Fig 5. Test circuit for resistive load switching

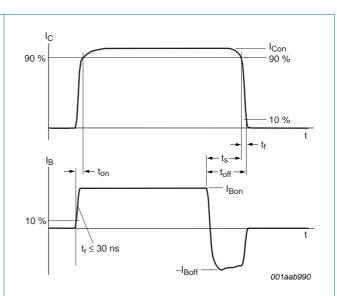
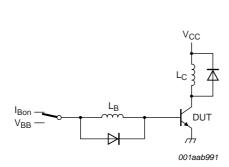


Fig 6. Switching times waveforms for resistive load



 $V_{CC}$  = 300 V;  $V_{BB}$  = –5 V;  $L_{C}$  = 200  $\mu H; \ L_{B}$  = 1  $\mu H.$ 

Fig 7. Test circuit for inductive load switching

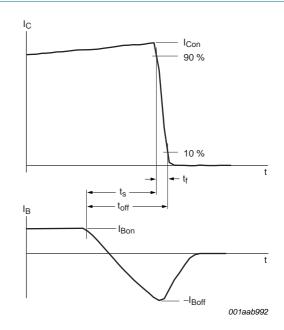


Fig 8. Switching times waveforms for inductive load

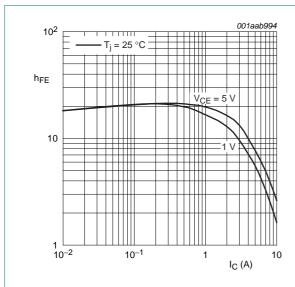


Fig 9. DC current gain as a function of collector current; typical values

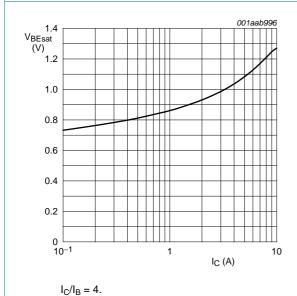
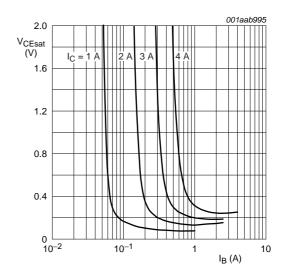
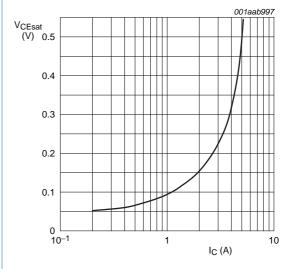


Fig 11. Base-emitter saturation voltage as a function of collector current; typical values



 $T_j = 25 \, ^{\circ}C$ .

Fig 10. Collector-emitter saturation voltage as a function of base current; typical values

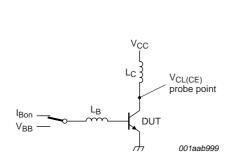


 $I_{\rm C}/I_{\rm B}=4$ .

Fig 12. Collector-emitter saturation voltage as a function of collector current; typical values

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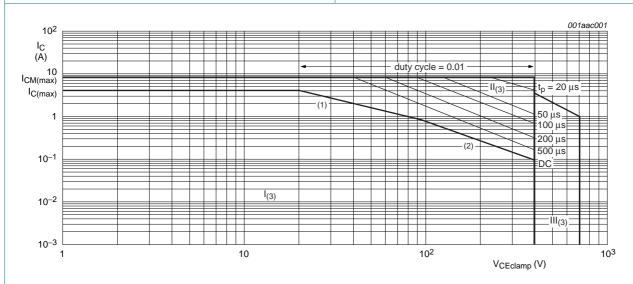
 $V_{CEclamp} \leq 1000 \text{ V; } V_{CC} = 150 \text{ V; } V_{BB} = -5 \text{ V; } L_B = 1 \text{ } \mu\text{H;}$ 

 $L_C = 200 \ \mu H.$ 

001aac000 10 I<sub>C</sub> (A) 8 6 4 2 0 200 400 600 1000 V<sub>CEclamp</sub> (V)

 $T_j \leq T_{j(max)}.$ 

Fig 13. Test circuit for reverse bias safe operating Fig 14. Reverse bias safe operating area



 $T_{mb}$   $\leq$  25 °C; Mounted with heatsink compound and 30  $\pm$  5 Newton force on the center of the envelope.

- (1) Ptot maximum and Ptot peak maximum lines.
- (2) Second breakdown limits.
- (3) I = Region of permissible DC operation.
  - II = Extension for repetitive pulse operation.
  - III = Extension during turn-on in single transistor converters provided that  $R_{BE} \le 100~\Omega$  and  $t_p \le 0.6~\mu s$ .

Fig 15. Forward bias safe operating area

#### **Package information** 7.

Epoxy meets requirements of UL94 V-0 at ½ inch.

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# Package outline

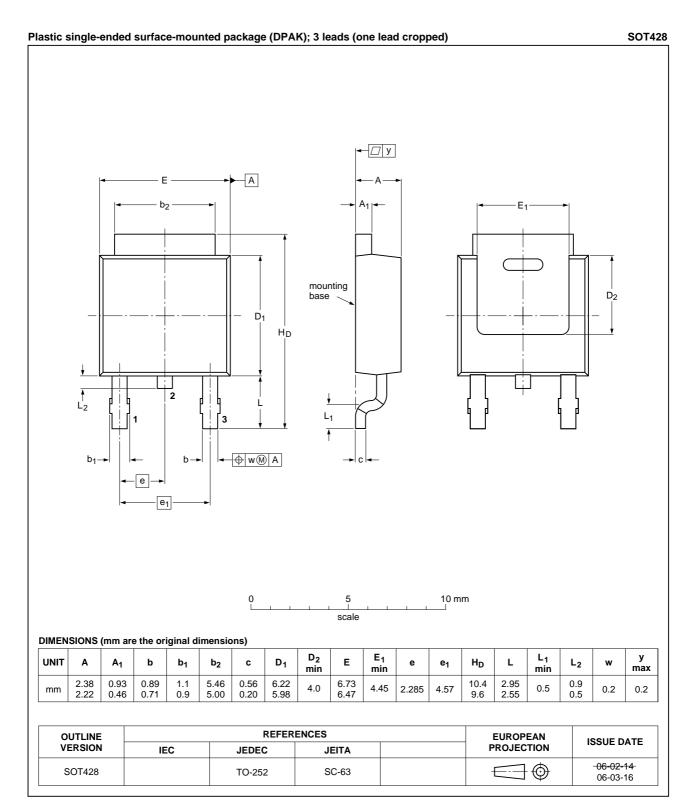


Fig 16. Package outline SOT428 (SC-63)

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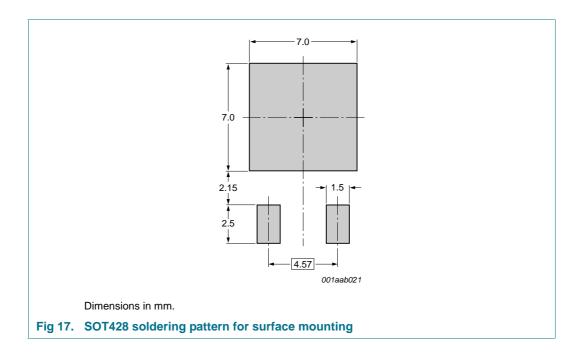
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# 9. Mounting



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# 10. Revision history

### Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUJ103AD v.2	20111108	Product data sheet	-	BUJ103AD v.1
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>			vith the new identity
	<ul> <li>Legal texts</li> </ul>	have been adapted to the	new company name whe	ere appropriate.
BUJ103AD v.1	20041214	Product data sheet	-	-

# 11. Legal information

#### 11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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